



Study on the Characteristics of Low Temperature Chemical Vapor Deposited Silicon Nitride and Silicon Oxide Film in through Silicon via Bumping Process

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A multi-chip stacked package using through silicon vias(TSVs) has the reliability concerns due to backside bump structure early in development. This paper introduces robust back-side bump structure for mechanical reliability of TSV multi-chip stack packages. Also, this paper presents the development of new passivation film for robust backside bump for TSV which can be formed at low temperature. The discussion focuses on the improvement of a variety of failure in application process of the film.

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